

#### **DUAL P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

# **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-30V	45mΩ @ V <sub>GS</sub> = -10V	-6.9A
	65mΩ @ V <sub>GS</sub> = -4.5V	-5.1A

# **Description**

This new generation MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# **Applications**

- **Power Management Functions**
- Backlighting
- DC-DC Converters

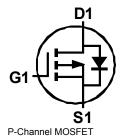
### SO-8 8 D1 7 D1 6 D2 G2 4 5 D2 TOP VIEW TOP VIEW Internal Schematic

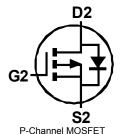
#### **Features**

- **Dual P-Channel MOSFET**
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072g (approximate)





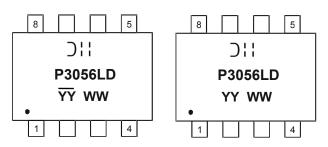
### Ordering Information (Note 4)

ſ	Part Number	Case	Packaging
	DMP3056LSD-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



Shanghai A/T Site

⊃¦¦ = Manufacturer's Marking P3056LD = Product Type Marking Code YYWW = Date Code Marking YY or  $\overline{YY}$  = Year (ex: 14 = 2014) WW = Week (01 - 53) YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)

YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Chengdu A/T Site



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Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-6.9 -5.8	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-24	A

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	50	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

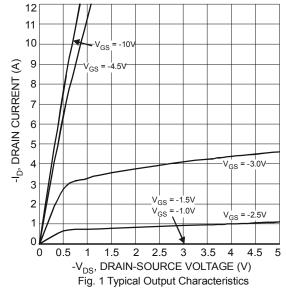
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Cumhal	Min	T	Moss	11!4	Took Condition	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	5.7			1		Tr. 2011 272 1	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			-1	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
Gate-Gource Leakage	IGSS			±800		$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	-1.7	-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance			_	45	0	$V_{GS} = -10V, I_D = -6.0A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>		_	65	mΩ	$V_{GS} = -4.5V, I_{D} = -5.0A$	
Forward Transconductance	9fs	_	8	_	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -5.3A	
Diode Forward Voltage (Note 7)	$V_{SD}$	-0.5	_	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.7A	
DYNAMIC CHARACTERISTICS						•	
Input Capacitance	C <sub>iss</sub>	_	722	_	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V	
Output Capacitance	Coss	_	114	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	92	_	pF	f = 1.0MHz	
Gate Resistance	$R_{G}$	_	3.3	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ f = 1.0MHz	
SWITCHING CHARACTERISTICS						•	
	$Q_G$	_	6.8	_	nC	$V_{DS} = -15V, V_{GS} = -4.5V,$	
Total Gate Charge			13.7			I <sub>D</sub> = -6A	
0.4.0	$Q_G$				_	$V_{DS} = -15V$ , $V_{GS} = -10V$ , $I_{D} = -6A$	
Gate-Source Charge	Q <sub>GS</sub>		1.6	_	nC		
Gate-Drain Charge	$Q_GD$	_	4.2	_		D -	
Turn-On Delay Time	t <sub>d(on)</sub>	_	6.4				
Rise Time	t <sub>r</sub>	_	5.3	_	ns	$V_{DS} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t <sub>d(off)</sub>	_	26.5	_	115	$I_D = -1A, R_G = 6.0\Omega$	
Fall Time	t <sub>f</sub>	_	14.7	_			

5. Device mounted on 2 oz. 1" x 1" Copper pads on 2" x 2" FR-4 PCB. 6. Pulse width  $\leq$ 10 $\mu$ S, Duty Cycle  $\leq$ 1%. Notes:

7. Short duration pulse test used to minimize self-heating effect.





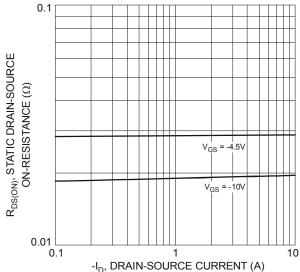
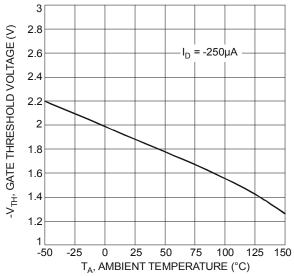
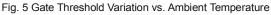
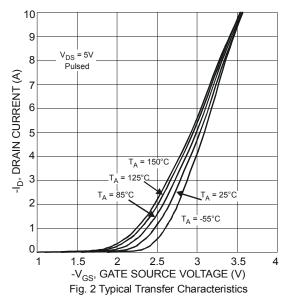


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage







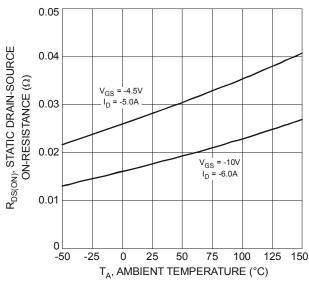
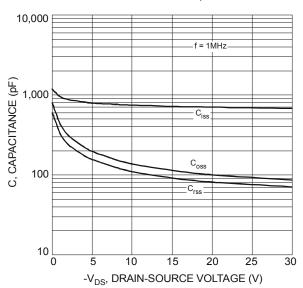
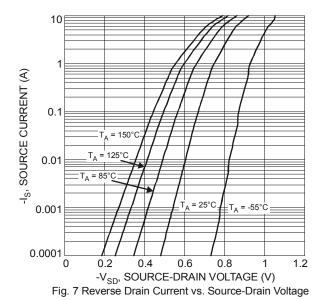


Fig. 4 Static Drain-Source On-Resistance vs. Ambient Temperature

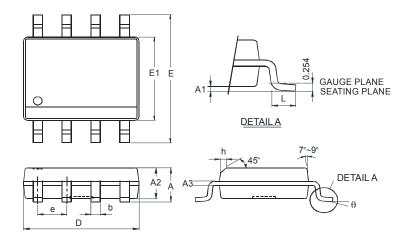






# **Package Outline Dimensions**

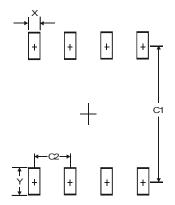
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8					
Dim	Min	Max			
Α	-	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	-	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Х	0.60		
Y	1.55		
C1	5.4		
C2	1.27		



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